Schottky barrier diode
RB425D / RB421D

●Applications

Low power rectification

●Features

1) Small surface mounting type. (SMD3)
2) High reliability.
3) Low reverse current and low forward voltage.

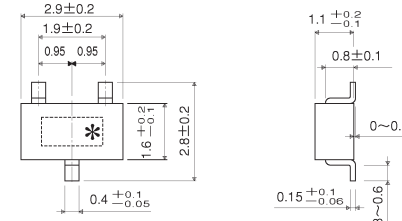
●Construction

Silicon epitaxial planar

●Marking

RB425D	D3L
RB421D	D3C

●External dimensions (Units: mm)



(All leads have the same dimensions)
＊Marking
RB425D : D3L
RB421D : D3C

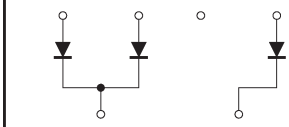
ROHM : SMD3
EIAJ : SC - 59
JEDEC : SOT - 23 similar

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	20	V
DC reverse voltage	V_R	10	V
Mean rectifying current	I_O	0.1	A
Peak forward surge curren*	I_{FSM}	1	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40～+125	℃

＊60 Hz for 1 ∿

●Equivalent circuits



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.45	0.55	V	I_F=100mA
Forward voltage	V_{F2}	—	0.28	0.34	V	I_F=10mA
Reverse current	I_R	—	1.0	30	μA	V_R=10V
Capacitance between terminals	C_T	—	6.0	—	pF	V_R=10V, f=1MHz

＊ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

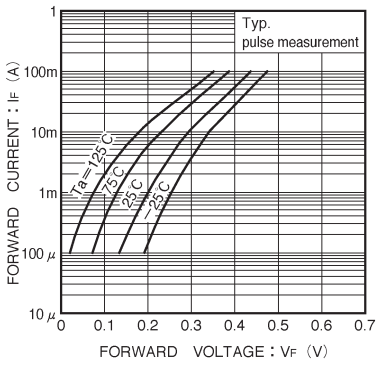


Fig. 1 Forward characteristics

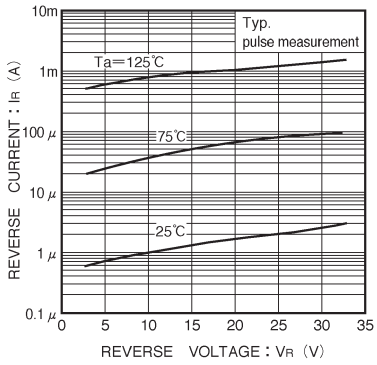


Fig. 2 Reverse characteristics

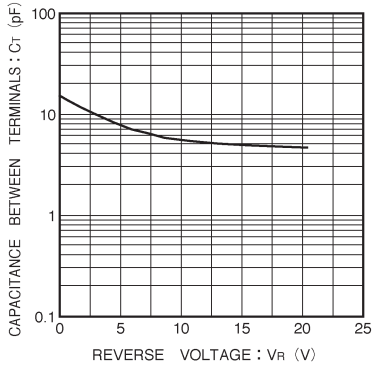


Fig. 3 Capacitance between terminals characteristics

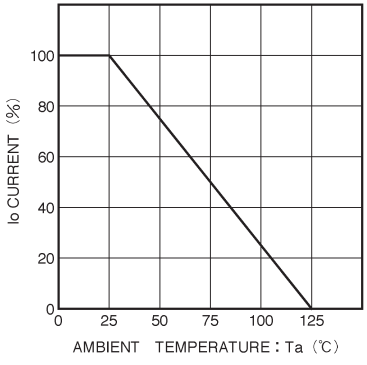


Fig. 4 Derating curve
(mounting on glass epoxy PCBs)